

RBA013N08R1SBPW

REXFET-1 N-Channel [Power MOSFET](#)

80 V - 340 A - 1.3 mΩ - TOLT for Automotive

Description

The RBA013N08R1SBPW N-channel power MOSFET features REXFET-1 split-gate technology and is offered in a TOLT package. The TOLT package features top-side cooling for ultra-compact and optimal thermal performance. Renesas' REXFET-1 split gate technology is suitable for applications requiring low $R_{DS(on)}$ and switching capability for high-power and high-frequency applications.

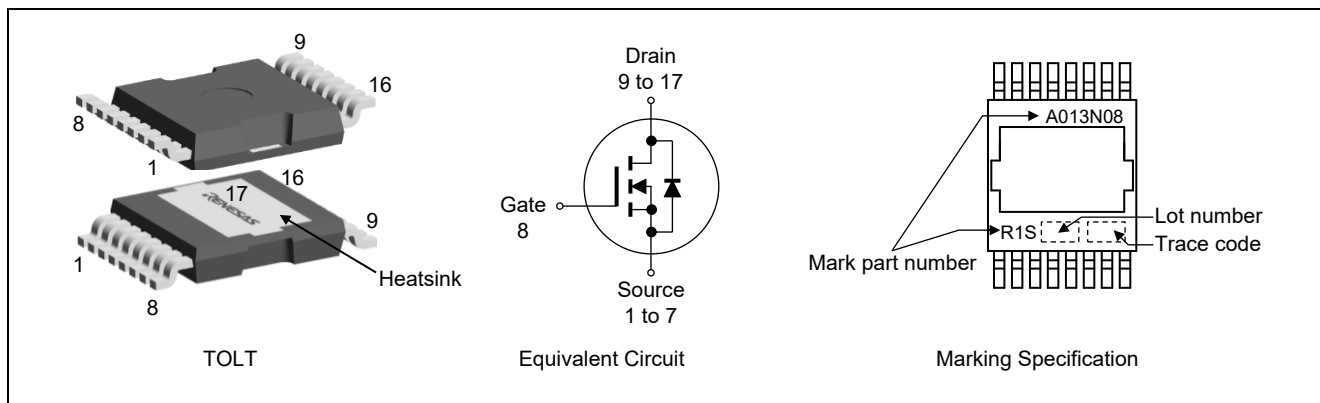
Features

- Standard level gate drive voltage: $V_{GS(th)} = 2.0$ to 4.0 V
- Super low on-state resistance: $R_{DS(on)} = 1.3$ mΩ Max.
- Low input capacitance
- Low thermal resistance
- 100% Avalanche tested
- AEC-Q101 qualified, PPAP capable
- Pb-free lead plating: RoHS compliant
- MSL1 classified according to IPC/JEDEC J-STD-020

Application

Small Traction (2-wheel, 3-wheel vehicle), 48 V load, Onboard charger, Charging station, Low voltage DC/DC

Outline



Absolute Maximum Ratings

($T_j = 25^\circ\text{C}$ unless otherwise notice.)

Item	Symbol	Ratings	Unit
Drain to Source Voltage	V_{DS}	80	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current (DC)	$I_D(DC)$ $T_C=25^\circ\text{C}$ Note 2,6	± 340	A
	$I_D(DC)$ $T_C=100^\circ\text{C}$ Note 2,6	± 296	A
Drain Current (pulse)	$I_D(pulse)$ Note 1,3,6	± 1360	A
Power Dissipation	P_D Note 1,6	468	W
Operating Junction Temperature	T_j	-55 to 175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 175	$^\circ\text{C}$
Single Avalanche Current	I_{AS} Note 4	69	A
Single Avalanche Energy	E_{AS} Note 4	476	mJ

Thermal Resistance

Item	Symbol	Max.	Unit
Junction to Case Thermal Resistance	$R_{th(j-c)}$ ^{Note 6}	0.32	°C/W
Junction to Ambient Thermal Resistance	$R_{th(j-a)}$ ^{Note 5,6}	40	°C/W

Electrical Characteristics

(T_j = 25 °C unless otherwise notice.)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}	—	—	10	μA	V _{DS} = 80 V, V _{GS} = 0 V
Gate Leakage Current	I_{GSS}	—	—	±100	nA	V _{GS} = ± 20 V, V _{DS} = 0 V
Gate to Source Threshold Voltage	V _{GS(th)}	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250 μA
Drain to Source On-state Resistance	R _{DS(on)}	—	1.16	1.3	mΩ	V _{GS} = 10 V, I _D = 100 A
Input Capacitance	C _{iss}	—	14000	—	pF	V _{DS} = 40 V
Output Capacitance	C _{oss}	—	2100	—	pF	V _{GS} = 0 V
Reverse Transfer Capacitance	C _{rss}	—	70	—	pF	f = 100 kHz
Gate resistance	R _g	—	1.8	—	Ω	—
Turn-on Delay Time	t _{d(on)}	—	70	—	ns	V _{DD} = 40 V
Rise Time	t _r	—	45	—	ns	I _D = 100 A
Turn-off Delay Time	t _{d(off)}	—	125	—	ns	V _{GS} = 10 V
Fall Time	t _f	—	50	—	ns	R _G = 5 Ω
Total Gate Charge	Q _g	—	185	—	nC	V _{DD} = 40 V
Gate to Source Charge	Q _{gs}	—	74	—	nC	V _{GS} = 10 V
Gate to Drain Charge	Q _{gd}	—	32	—	nC	I _D = 100 A
Gate plateau voltage	V _{plateau}	—	5.4	—	V	
Output Charge	Q _{oss}	—	180	—	nC	V _{DD} = 40 V, V _{GS} = 0 V
Body Diode Forward Voltage	V _{F(S-D)}	—	0.84	1.5	V	I _F = 100 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}	—	100	—	ns	I _F = 100 A, V _{GS} = 0 V
Reverse Recovery Charge	Q _{rr}	—	255	—	nC	di/dt = 100 A/μs

Note 1. T_c = 25 °C

2. Value is limited by overall system design including PCB.

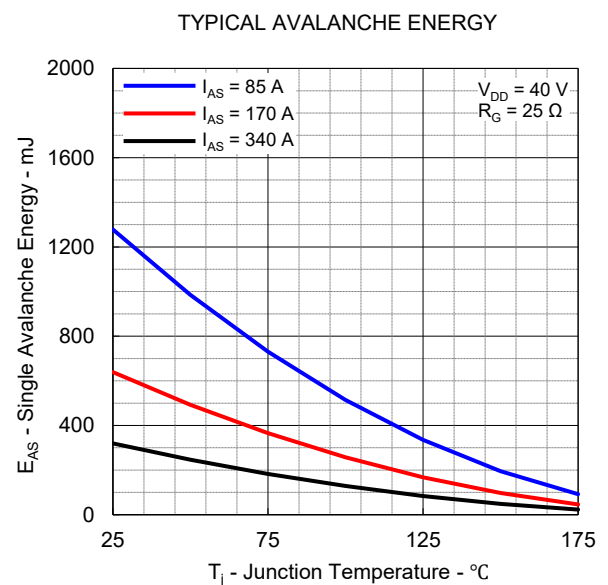
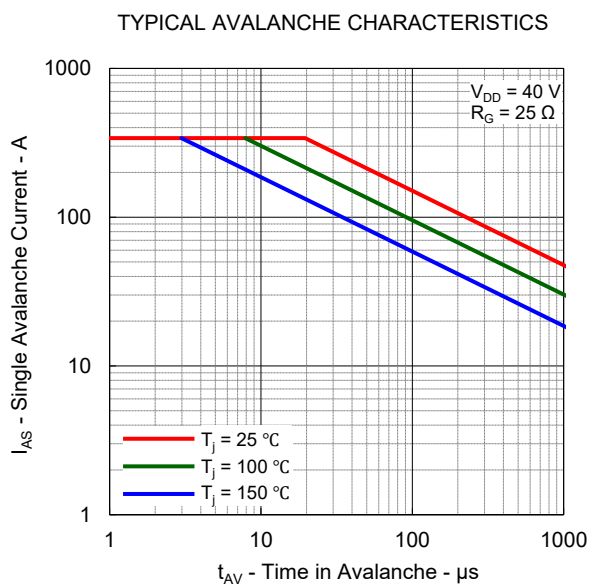
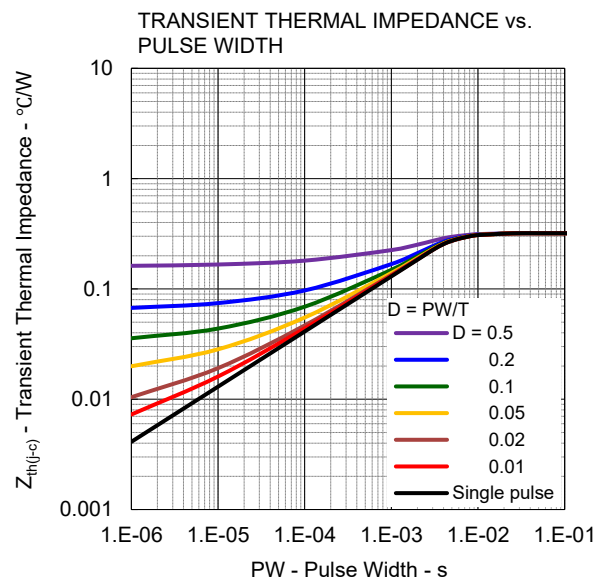
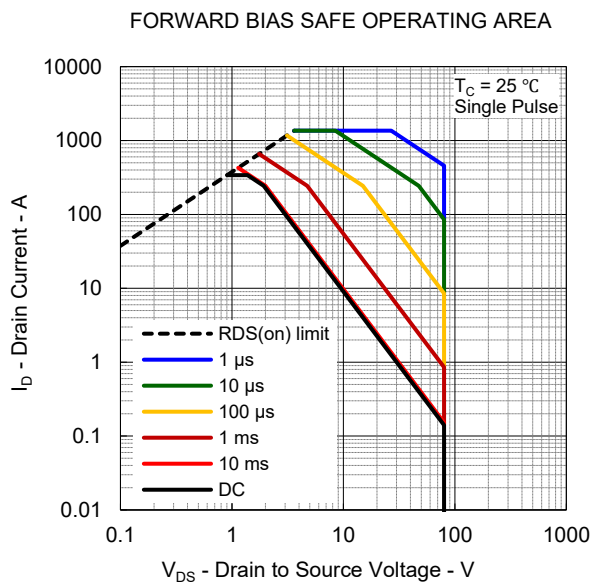
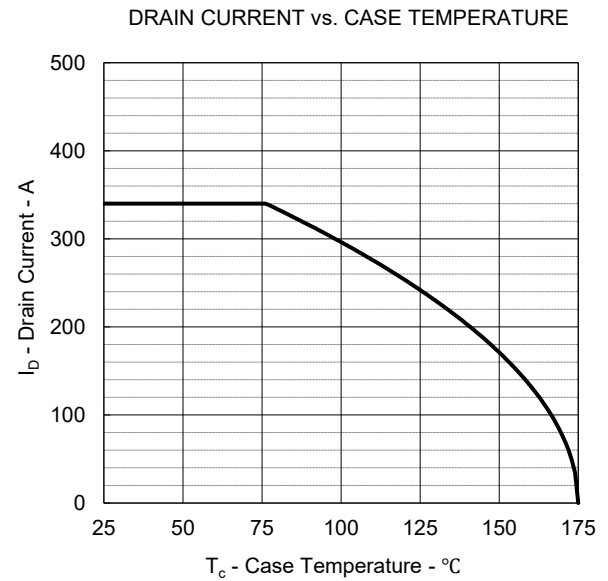
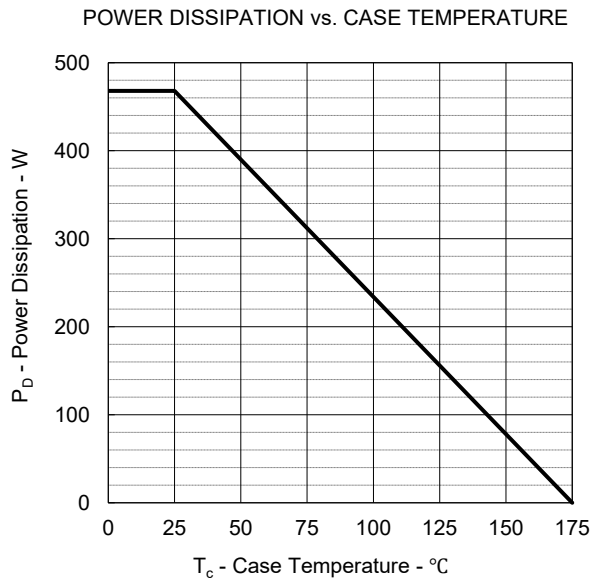
3. PW ≤ 10 μs

4. L = 100 μH, V_{DD} = 40 V, R_G = 25 Ω

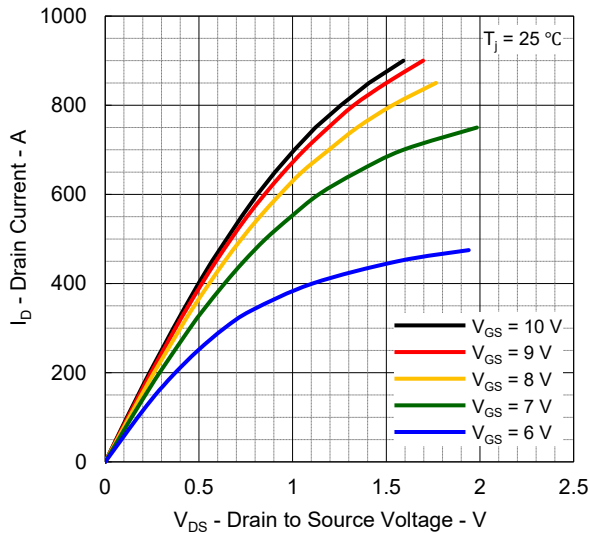
5. Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4. (2 oz Cu pad.)

6. Defined by design. Not subject to production test.

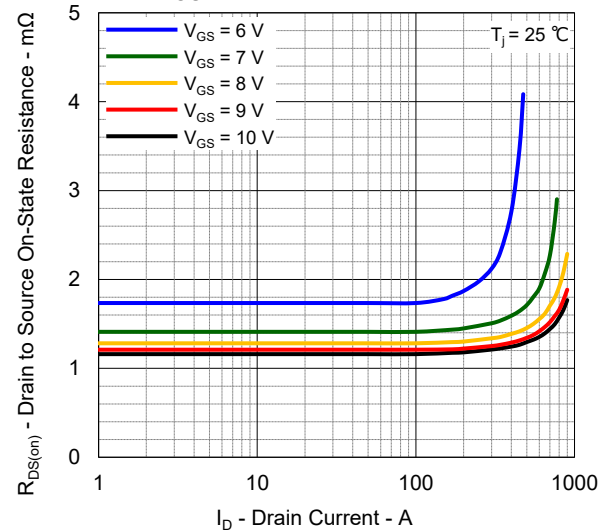
Typical Characteristics



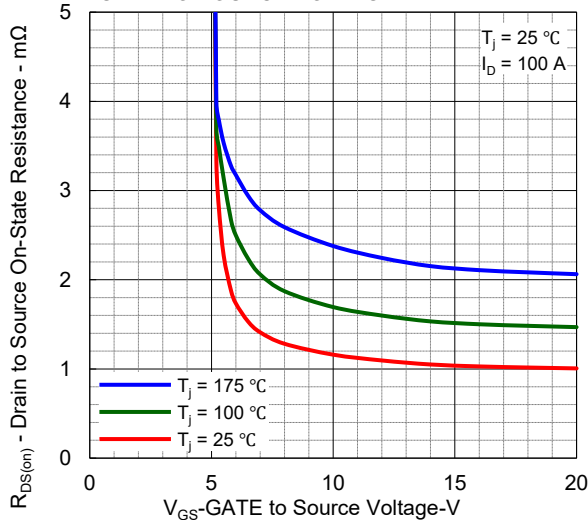
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



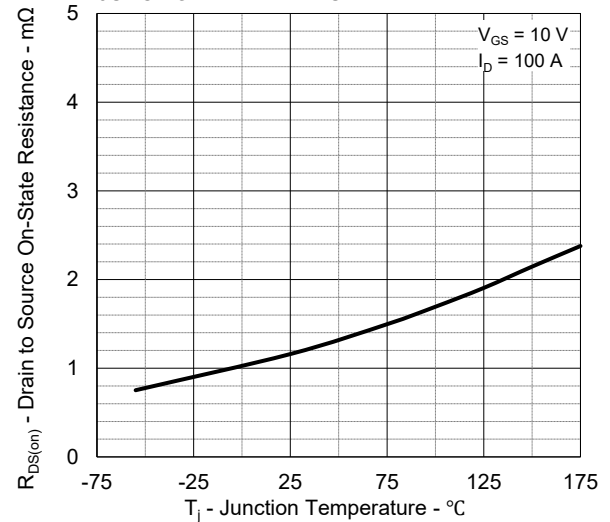
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



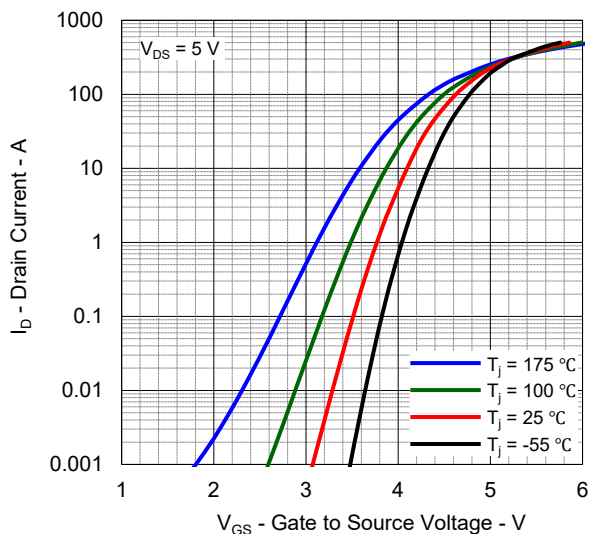
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



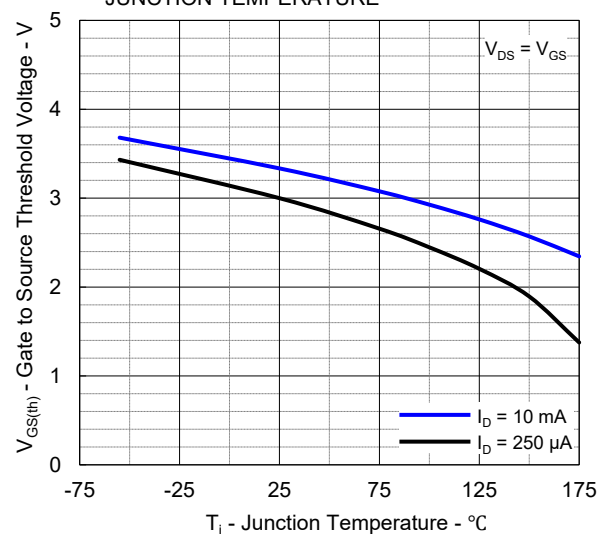
DRAIN TO SOURCE ON-STATE RESISTANCE vs. JUNCTION TEMPERATURE



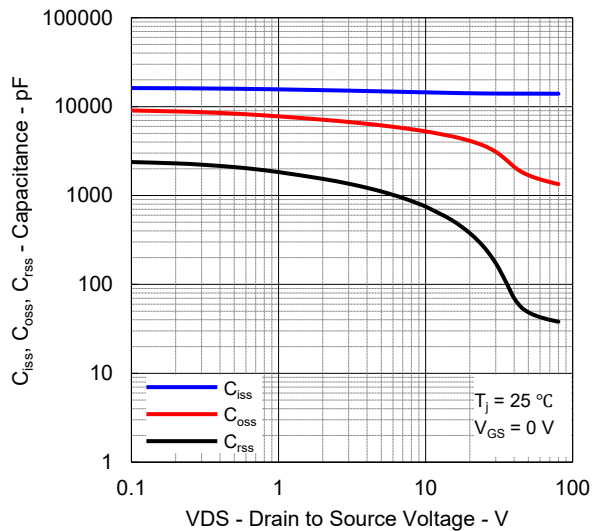
FORWARD TRANSFER CHARACTERISTICS



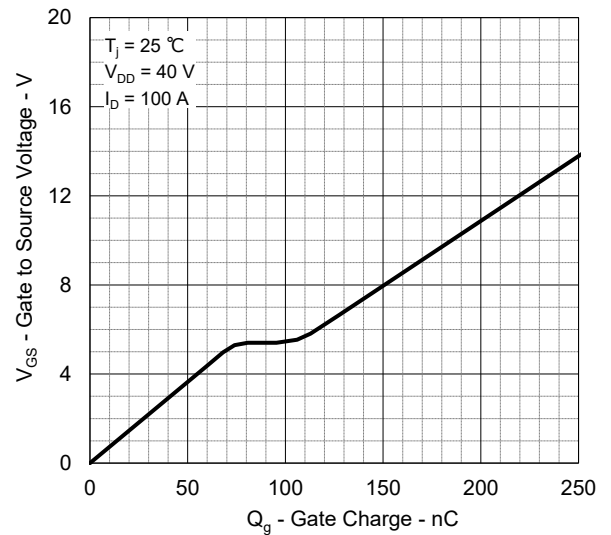
GATE TO SOURCE THRESHOLD VOLTAGE vs. JUNCTION TEMPERATURE



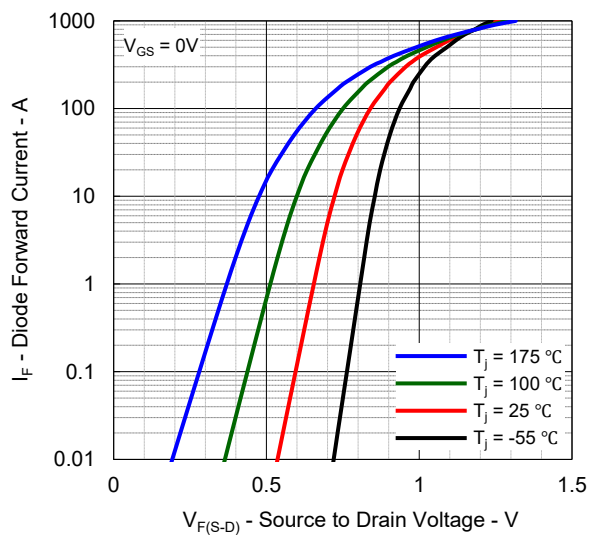
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



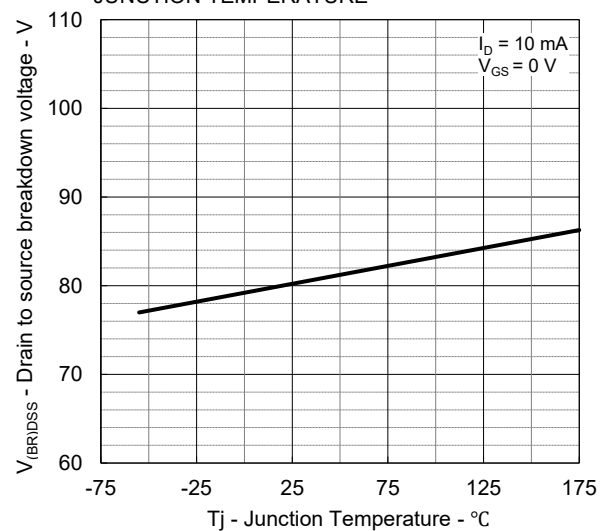
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

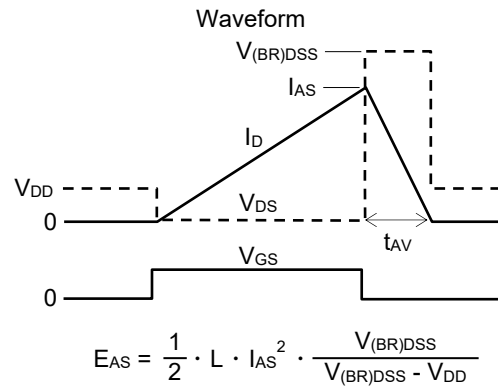
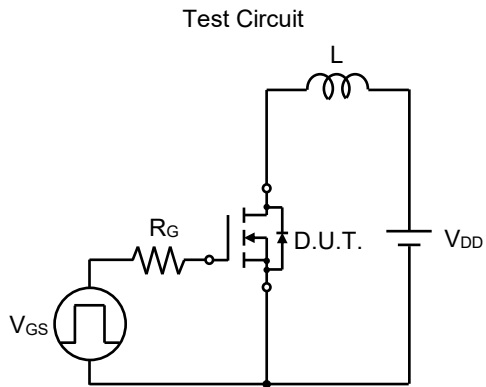


DRAIN TO SOURCE BREAKDOWN VOLTAGE vs. JUNCTION TEMPERATURE

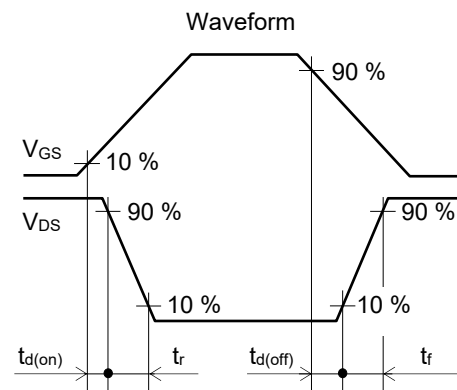
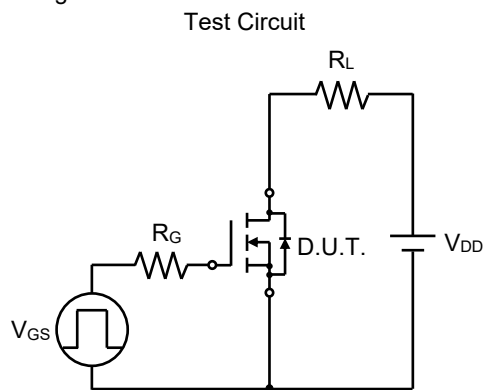


Test Circuit

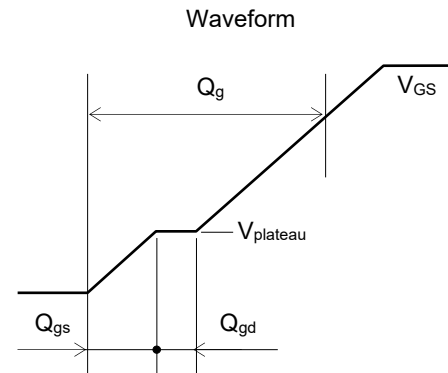
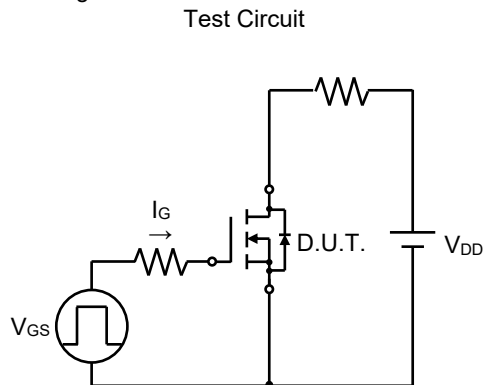
Avalanche



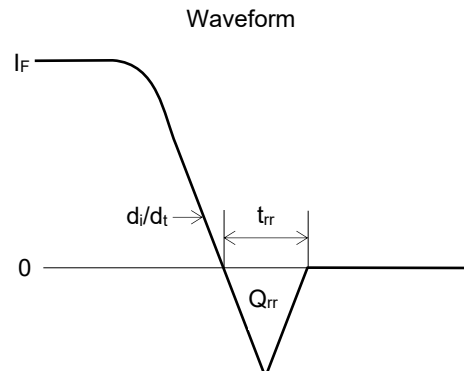
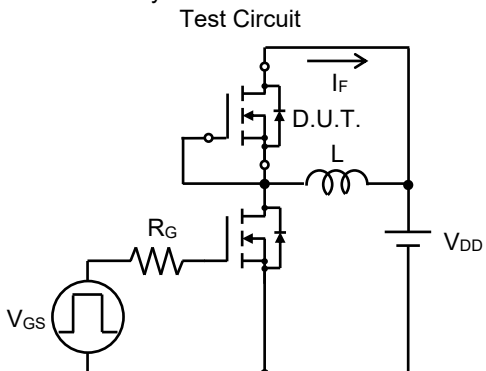
Switching Time



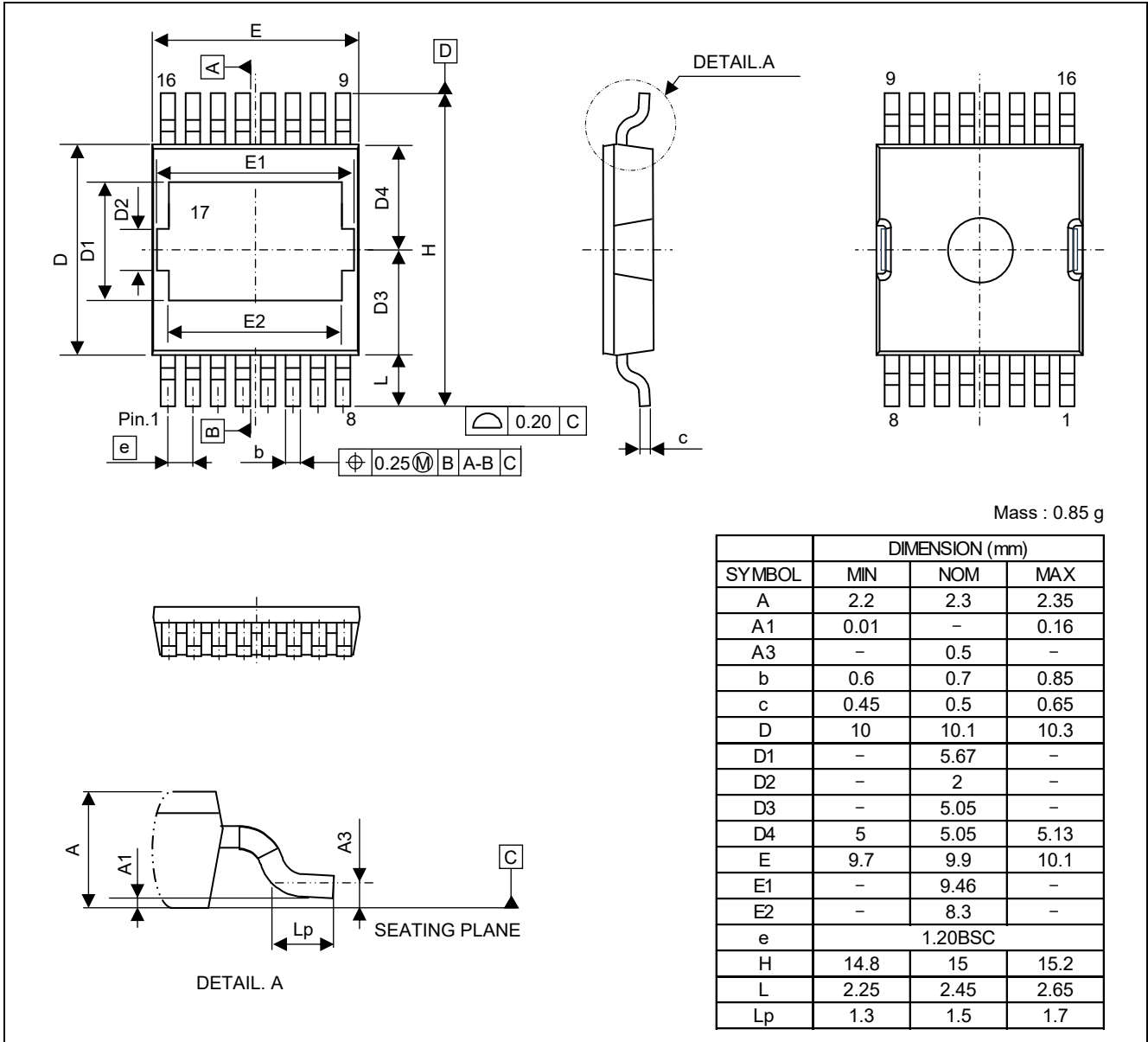
Gate Charge



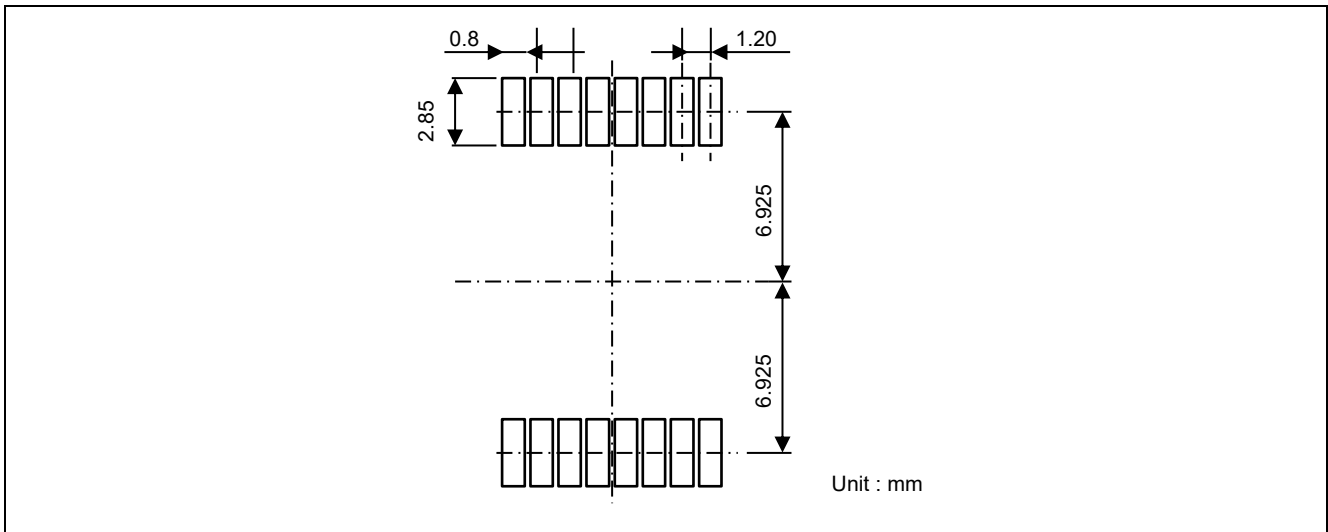
Reverse Recovery



Package Dimensions



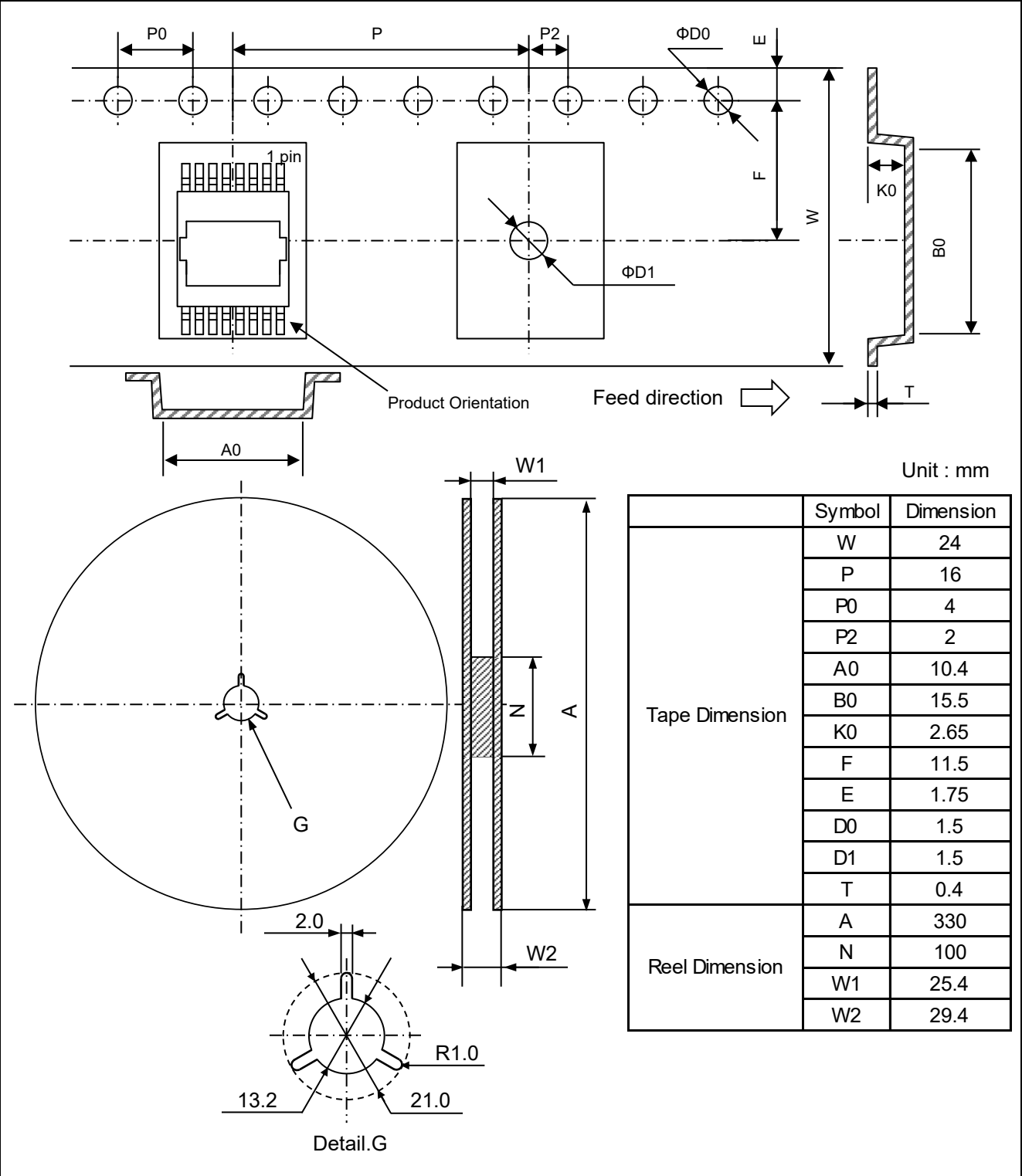
Mount pad



Ordering Information

Part No.	Packing	Quantity
RBA013N08R1SBPW#KB0	Taping	1300pcs/reel

Packing Specification



Remark : Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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